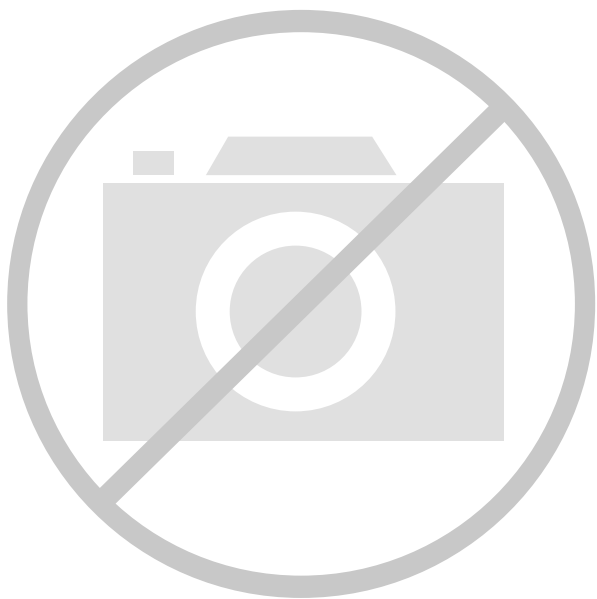




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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	848
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	151
Number of Gates	6000
Voltage - Supply	4.5V ~ 5.5V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	176-LQFP
Supplier Device Package	176-TQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/a1460a-tq176c

Antifuse Connections

An antifuse is a “normally open” structure as opposed to the normally closed fuse structure used in PROMs or PALs. The use of antifuses to implement a programmable logic device results in highly testable structures as well as an efficient programming architecture. The structure is highly testable because there are no preexisting connections; temporary connections can be made using pass transistors. These temporary connections can isolate individual antifuses to be programmed as well as isolate individual circuit structures to be tested. This can be done both before and after programming. For example, all metal tracks can be tested for continuity and shorts between adjacent tracks, and the functionality of all logic modules can be verified.

Four types of antifuse connections are used in the routing structure of the ACT 3 array. (The physical structure of the antifuse is identical in each case; only the usage differs.)

Table 2-1 shows four types of antifuses.

Table 2-1 • Antifuse Types

Type	Description
XF	Horizontal-to-vertical connection
HF	Horizontal-to-horizontal connection
VF	Vertical-to-vertical connection
FF	"Fast" vertical connection

Examples of all four types of connections are shown in Figure 2-7 on page 2-6 and Figure 2-8 on page 2-6.

Module Interface

Connections to Logic and I/O modules are made through vertical segments that connect to the module inputs and outputs. These vertical segments lie on vertical tracks that span the entire height of the array.

Module Input Connections

The tracks dedicated to module inputs are segmented by pass transistors in each module row. During normal user operation, the pass transistors are inactive, which isolates the inputs of a module from the inputs of the module directly above or below it. During certain test modes, the pass transistors are active to verify the continuity of the metal tracks. Vertical input segments span only the channel above or the channel below. The logic modules are arranged such that half of the inputs are connected to the channel above and half of the inputs to segments in the channel below, as shown in Figure 2-9.

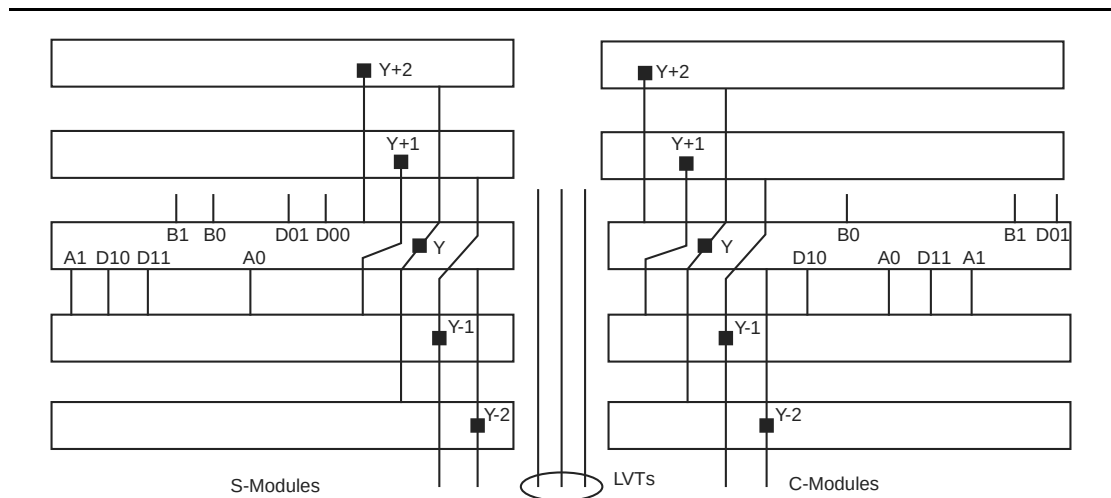


Figure 2-9 • Logic Module Routing Interface

Module Output Connections

Module outputs have dedicated output segments. Output segments extend vertically two channels above and two channels below, except at the top or bottom of the array. Output segments twist, as shown in Figure 10, so that only four vertical tracks are required.

LVT Connections

Outputs may also connect to nondedicated segments called Long Vertical Tracks (LVTs). Each module pair in the array shares four LVTs that span the length of the column. Any module in the column pair can connect to one of the LVTs in the column using an FF connection. The FF connection uses antifuses connected directly to the driver stage of the module output, bypassing the isolation transistor. FF antifuses are programmed at a higher current level than HF, VF, or XF antifuses to produce a lower resistance value.

Antifuse Connections

In general every intersection of a vertical segment and a horizontal segment contains an unprogrammed antifuse (XF-type). One exception is in the case of the clock networks.

Clock Connections

To minimize loading on the clock networks, a subset of inputs has antifuses on the clock tracks. Only a few of the C-module and S-module inputs can be connected to the clock networks. To further reduce loading on the clock network, only a subset of the horizontal routing tracks can connect to the clock inputs of the S-module.

Programming and Test Circuits

The array of logic and I/O modules is surrounded by test and programming circuits controlled by the temporary special I/O pins MODE, SDI, and DCLK. The function of these pins is similar to all ACT family devices. The ACT 3 family also includes support for two Actionprobe[®] circuits, allowing complete observability of any logic or I/O module in the array using the temporary special I/O pins, PRA and PRB.

5 V Operating Conditions

Table 2-2 • Absolute Maximum Ratings¹, Free Air Temperature Range

Symbol	Parameter	Limits	Units
VCC	DC supply voltage	–0.5 to +7.0	V
VI	Input voltage	–0.5 to VCC + 0.5	V
VO	Output voltage	–0.5 to VCC + 0.5	V
IIO	I/O source sink current ²	±20	mA
T _{STG}	Storage temperature	–65 to +150	°C

Notes:

- Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended periods may affect device reliability. Device should not be operated outside the recommended operating conditions.
- Device inputs are normally high impedance and draw extremely low current. However, when input voltage is greater than VCC + 0.5 V for less than GND –0.5 V, the internal protection diodes will forward bias and can draw excessive current.

Table 2-3 • Recommended Operating Conditions

Parameter	Commercial	Industrial	Military	Units
Temperature range*	0 to +70	–40 to +85	–55 to +125	°C
5 V power supply tolerance	±5	±10	±10	%VCC

Note: *Ambient temperature (T_A) is used for commercial and industrial; case temperature (T_C) is used for military.

Table 2-4 • Electrical Specifications

Symbol	Parameter	Test Condition	Commercial		Industrial		Military		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
VOH ^{1,2}	High level output	IOH = –4 mA (CMOS)	–	–	3.7	–	3.7	–	V
		IOH = –6 mA (CMOS)	3.84						V
		IOH = –10 mA (TTL) ³	2.40						V
VOL ^{1,2}	Low level output	IOL = +6 mA (CMOS)		0.33		0.4		0.4	V
		IOL = +12 mA (TTL) ³		0.50					
VIH	High level input	TTL inputs	2.0	VCC + 0.3	2.0	VCC + 0.3	2.0	VCC + 0.3	V
VIL	Low level input	TTL inputs	–0.3	0.8	–0.3	0.8	–0.3	0.8	V
IIN	Input leakage	VI = VCC or GND	–10	+10	–10	+10	–10	+10	μA
IOZ	3-state output leakage	VO = VCC or GND	–10	+10	–10	+10	–10	+10	μA
C _{IO}	I/O capacitance ^{3,4}			10		10		10	pF
ICC(S)	Standby VCC supply current (typical = 0.7 mA)			2		10		20	mA
ICC(D)	Dynamic VCC supply current. See the Power Dissipation section.								

Notes:

- Microsemi devices can drive and receive either CMOS or TTL signal levels. No assignment of I/Os as TTL or CMOS is required.
- Tested one output at a time, VCC = minimum.
- Not tested; for information only.
- VOUT = 0 V, f = 1 MHz
- Typical standby current = 0.7 mA. All outputs unloaded. All inputs = VCC or GND.

3.3 V Operating Conditions

Table 2-5 • Absolute Maximum Ratings¹, Free Air Temperature Range

Symbol	Parameter	Limits	Units
VCC	DC supply voltage	−0.5 to +7.0	V
VI	Input voltage	−0.5 to VCC + 0.5	V
VO	Output voltage	−0.5 to VCC + 0.5	V
IIO	I/O source sink current ²	±20	mA
T _{STG}	Storage temperature	−65 to +150	°C

Notes:

- Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended periods may affect device reliability. Device should not be operated outside the recommended operating conditions.
- Device inputs are normally high impedance and draw extremely low current. However, when input voltage is greater than VCC + 0.5 V for less than GND −0.5 V, the internal protection diodes will forward bias and can draw excessive current.

Table 2-6 • Recommended Operating Conditions

Parameter	Commercial	Units
Temperature range*	0 to +70	°C
Power supply tolerance	3.0 to 3.6	V

Note: *Ambient temperature (T_A) is used for commercial.

Table 2-7 • Electrical Specifications

Parameter		Commercial		Units
		Min.	Max.	
VOH ¹	I _{OH} = −4 mA	2.15	–	V
	I _{OH} = −3.2 mA	2.4		V
VOL ¹	I _{OL} = 6 mA		0.4	V
VIL		−0.3	0.8	V
VIH		2.0	VCC + 0.3	V
Input transition time t _R , t _F ²	VI = VCC or GND	−10	+10	μA
C _{IO} I/O Capacitance ^{2,3}			10	pF
Standby current, I _{CC} ⁴ (typical = 0.3 mA)			0.75	mA
Leakage current ⁵		−10	10	μA

- Only one output tested at a time. VCC = minimum.
- Not tested; for information only.
- Includes worst-case 84-pin PLCC package capacitance. V_{OUT} = 0 V, f = 1 MHz.
- Typical standby current = 0.3 mA. All outputs unloaded. All inputs = VCC or GND.
- VO, VIN = VCC or GND

Package Thermal Characteristics

The device junction to case thermal characteristic is θ_{jc} , and the junction to ambient air characteristic is θ_{ja} . The thermal characteristics for θ_{ja} are shown with two different air flow rates.

Maximum junction temperature is 150°C.

A sample calculation of the absolute maximum power dissipation allowed for a CPGA 175-pin package at commercial temperature and still air is as follows:

$$\frac{\text{Max. junction temp. (°C)} - \text{Max. ambient temp. (°C)}}{\theta_{ja} \text{ °C/W}} = \frac{150^{\circ}\text{C} - 70^{\circ}\text{C}}{25^{\circ}\text{C/W}} = 3.2 \text{ W}$$

EQ 2

Table 2-8 • Package Thermal Characteristics

Package Type*	Pin Count	θ_{jc}	θ_{ja} Still Air	θ_{ja} 300 ft./min.	Units
Ceramic Pin Grid Array	100	20	35	17	°C/W
	133	20	30	15	°C/W
	175	20	25	14	°C/W
	207	20	22	13	°C/W
	257	20	15	8	°C/W
Ceramic Quad Flatpack	132	13	55	30	°C/W
	196	13	36	24	°C/W
	256	13	30	18	°C/W
Plastic Quad Flatpack	100	13	51	40	°C/W
	160	10	33	26	°C/W
	208	10	33	26	°C/W
Very Thin Quad Flatpack	100	12	43	35	°C/W
Thin Quad Flatpack	176	11	32	25	°C/W
Power Quad Flatpack	208	0.4	17	13	°C/W
Plastic Leaded Chip Carrier	84	12	37	28	°C/W
Plastic Ball Grid Array	225	10	25	19	°C/W
	313	10	23	17	°C/W

Note: Maximum power dissipation in still air:

PQ160 = 2.4 W

PQ208 = 2.4 W

PQ100 = 1.6 W

VQ100 = 1.9 W

TQ176 = 2.5 W

PL84 = 2.2 W

RQ208 = 4.7 W

BG225 = 3.2 W

BG313 = 3.5 W

Power Dissipation

$$P = [ICC_{\text{standby}} + I_{\text{active}}] * VCC * IOL * VOL * N + IOH * (VCC - VOH) * M$$

EQ 3

where:

ICC standby is the current flowing when no inputs or outputs are changing

Iactive is the current flowing due to CMOS switching.

IOL and IOH are TTL sink/source current.

VOL and VOH are TTL level output voltages.

N is the number of outputs driving TTL loads to VOL.

M equals the number of outputs driving TTL loads to VOH.

An accurate determination of N and M is problematical because their values depend on the design and on the system I/O. The power can be divided into two components: static and active.

Static Power Component

Microsemi FPGAs have small static power components that result in lower power dissipation than PALs or PLDs. By integrating multiple PALs/PLDs into one FPGA, an even greater reduction in board-level power dissipation can be achieved.

The power due to standby current is typically a small component of the overall power. Standby power is calculated in Table 2-9 for commercial, worst case conditions.

Table 2-9 • Standby Power Calculation

ICC	VCC	Power
2 mA	5.25 V	10.5 mW

The static power dissipated by TTL loads depends on the number of outputs driving high or low and the DC load current. Again, this value is typically small. For instance, a 32-bit bus sinking 4 mA at 0.33 V will generate 42 mW with all outputs driving low, and 140 mW with all outputs driving high. The actual dissipation will average somewhere between as I/Os switch states with time.

Active Power Component

Power dissipation in CMOS devices is usually dominated by the active (dynamic) power dissipation. This component is frequency dependent, a function of the logic and the external I/O. Active power dissipation results from charging internal chip capacitances of the interconnect, unprogrammed antifuses, module inputs, and module outputs, plus external capacitance due to PC board traces and load device inputs.

An additional component of the active power dissipation is the totem-pole current in CMOS transistor pairs. The net effect can be associated with an equivalent capacitance that can be combined with frequency and voltage to represent active power dissipation.

Equivalent Capacitance

The power dissipated by a CMOS circuit can be expressed by EQ 4.

$$\text{Power } (\mu\text{W}) = C_{\text{EQ}} * VCC^2 * F$$

EQ 4

Where:

C_{EQ} is the equivalent capacitance expressed in pF.

VCC is the power supply in volts.

F is the switching frequency in MHz.

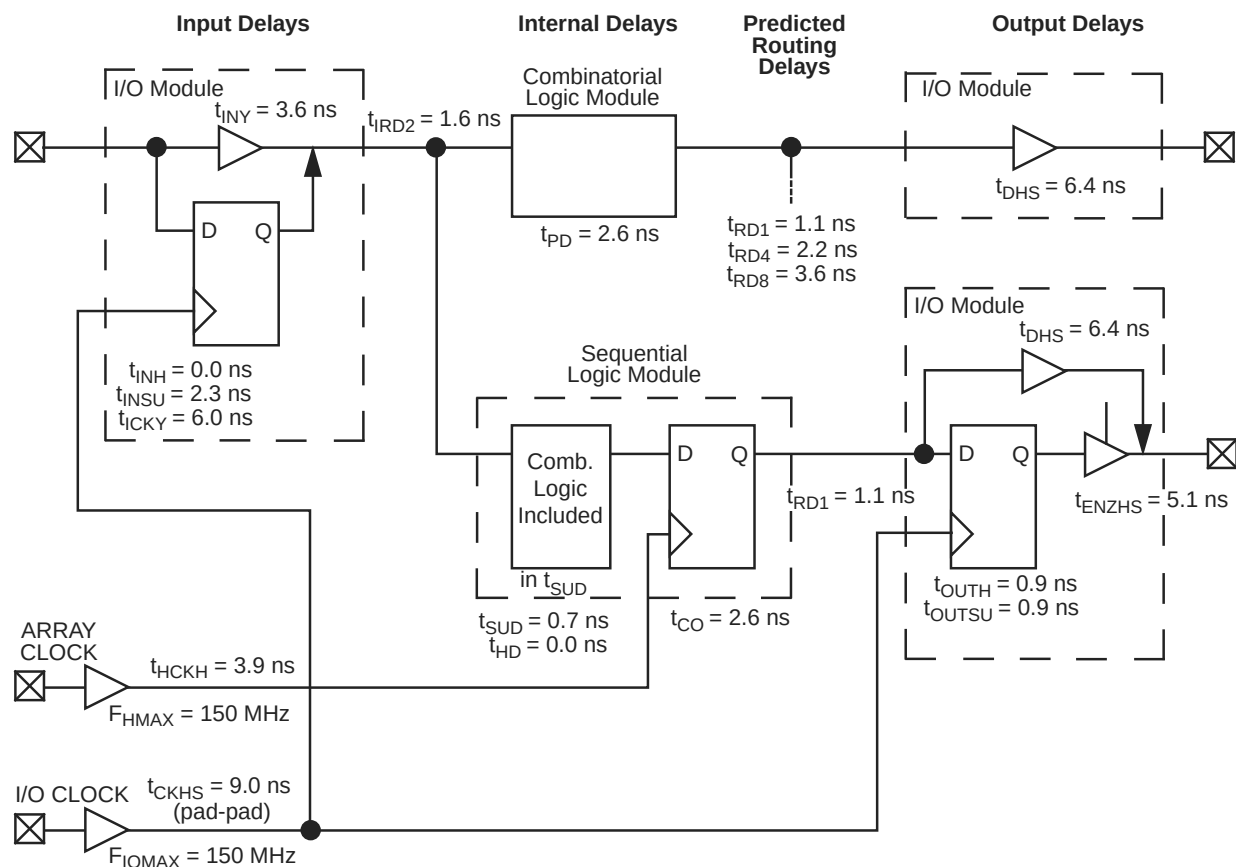
Determining Average Switching Frequency

To determine the switching frequency for a design, you must have a detailed understanding of the data input values to the circuit. The following guidelines are meant to represent worst-case scenarios so that they can be generally used to predict the upper limits of power dissipation. These guidelines are as follows:

Table 2-13 • Guidelines for Predicting Power Dissipation

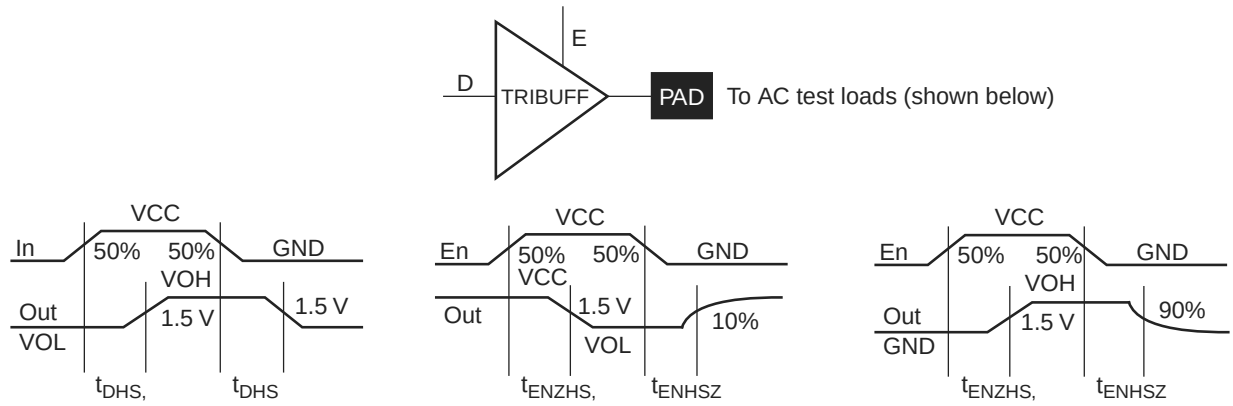
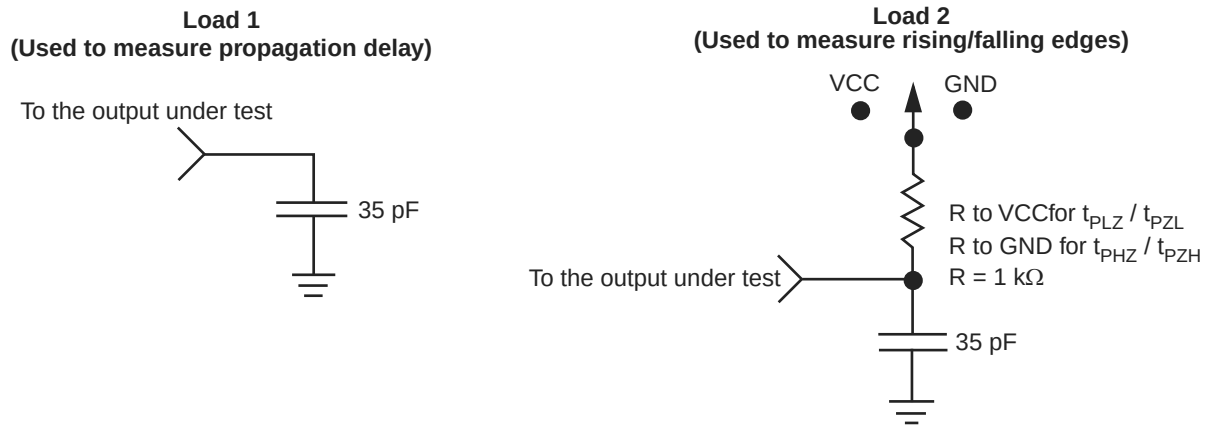
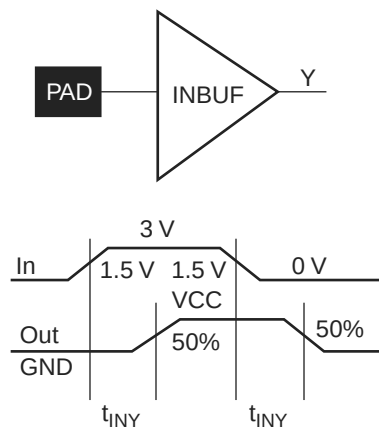
Data	Value
Logic Modules (m)	80% of modules
Inputs switching (n)	# inputs/4
Outputs switching (p)	# output/4
First routed array clock loads (q1)	40% of sequential modules
Second routed array clock loads (q2)	40% of sequential modules
Load capacitance (CL)	35 pF
Average logic module switching rate (fm)	F/10
Average input switching rate (fn)	F/5
Average output switching rate (fp)	F/10
Average first routed array clock rate (fq1)	F/2
Average second routed array clock rate (fq2)	F/2
Average dedicated array clock rate (fs1)	F
Average dedicated I/O clock rate (fs2)	F

ACT 3 Timing Model



Note: Values shown for A1425A -1 speed grade device.

Figure 2-10 • Timing Model


Figure 2-11 • Output Buffers

Figure 2-12 • AC Test Loads

Figure 2-13 • Input Buffer Delays

A1440A, A14V40A Timing Characteristics

Table 2-26 • A1440A, A14V40A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C¹

Logic Module Propagation Delays ²		–3 Speed ³		–2 Speed ³		–1 Speed		Std. Speed		3.3 V Speed ¹		Units
Parameter/Description		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
t _{PD}	Internal Array Module		2.0		2.3		2.6		3.0		3.9	ns
t _{CO}	Sequential Clock to Q		2.0		2.3		2.6		3.0		3.9	ns
t _{CLR}	Asynchronous Clear to Q		2.0		2.3		2.6		3.0		3.9	ns
Predicted Routing Delays⁴												
t _{RD1}	FO = 1 Routing Delay		0.9		1.0		1.1		1.3		1.7	ns
t _{RD2}	FO = 2 Routing Delay		1.2		1.4		1.6		1.8		2.4	ns
t _{RD3}	FO = 3 Routing Delay		1.4		1.6		1.8		2.1		2.8	ns
t _{RD4}	FO = 4 Routing Delay		1.7		1.9		2.2		2.5		3.3	ns
t _{RD8}	FO = 8 Routing Delay		2.8		3.2		3.6		4.2		5.5	ns
Logic Module Sequential Timing												
t _{SUD}	Flip-Flop Data Input Setup	0.5		0.6		0.7		0.8		0.8		ns
t _{HD}	Flip-Flop Data Input Hold	0.0		0.0		0.0		0.0		0.0		ns
t _{SUD}	Latch Data Input Setup	0.5		0.6		0.7		0.8		0.8		ns
t _{HD}	Latch Data Input Hold	0.0		0.0		0.0		0.0		0.0		ns
t _{WASYN}	Asynchronous Pulse Width	1.9		2.4		3.2		3.8		4.8		ns
t _{WCLKA}	Flip-Flop Clock Pulse Width	1.9		2.4		3.2		3.8		4.8		ns
t _A	Flip-Flop Clock Input Period	4.0		5.0		6.8		8.0		10.0		ns
f _{MAX}	Flip-Flop Clock Frequency		250		200		150		125		100	MHz

Notes:

- VCC = 3.0 V for 3.3 V specifications.
- For dual-module macros, use t_{PD} + t_{RD1} + t_{PDn} + t_{CO} + t_{RD1} + t_{PDn} or t_{PD1} + t_{RD1} + t_{SUD}, whichever is appropriate.
- The –2 and –3 speed grades have been discontinued. Refer to PDN 0104, PDN 0203, PDN 0604, and PDN 1004 at <http://www.microsemi.com/soc/support/notifications/default.aspx#pdn>.
- Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing analysis or simulation is required to determine actual worst-case performance. Post-route timing is based on actual routing delay measurements performed on the device prior to shipment.

A1440A, A14V40A Timing Characteristics (continued)

Table 2-27 • A1440A, A14V40A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C

I/O Module Input Propagation Delays		–3 Speed ¹		–2 Speed ¹		–1 Speed		Std. Speed		3.3 V Speed ¹		Units
Parameter/Description		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
t _{INY}	Input Data Pad to Y		2.8		3.2		3.6		4.2		5.5	ns
t _{ICKY}	Input Reg IOCLK Pad to Y		4.7		5.3		6.0		7.0		9.2	ns
t _{OCKY}	Output Reg IOCLK Pad to Y		4.7		5.3		6.0		7.0		9.2	ns
t _{ICLRY}	Input Asynchronous Clear to Y		4.7		5.3		6.0		7.0		9.2	ns
t _{OCLRY}	Output Asynchronous Clear to Y		4.7		5.3		6.0		7.0		9.2	ns
Predicted Input Routing Delays²												
t _{RD1}	FO = 1 Routing Delay		0.9		1.0		1.1		1.3		1.7	ns
t _{RD2}	FO = 2 Routing Delay		1.2		1.4		1.6		1.8		2.4	ns
t _{RD3}	FO = 3 Routing Delay		1.4		1.6		1.8		2.1		2.8	ns
t _{RD4}	FO = 4 Routing Delay		1.7		1.9		2.2		2.5		3.3	ns
t _{RD8}	FO = 8 Routing Delay		2.8		3.2		3.6		4.2		5.5	ns
I/O Module Sequential Timing (wrt IOCLK pad)												
t _{INH}	Input F-F Data Hold	0.0		0.0		0.0		0.0		0.0		ns
t _{INSU}	Input F-F Data Setup	1.8		1.7		2.0		2.3		2.3		ns
t _{IDEH}	Input Data Enable Hold	0.0		0.0		0.0		0.0		0.0		ns
t _{IDESU}	Input Data Enable Setup	5.8		6.5		7.5		8.6		8.6		ns
t _{OUTH}	Output F-F Data hold	0.7		0.8		0.9		1.0		1.0		ns
t _{OUTSU}	Output F-F Data Setup	0.7		0.8		0.9		1.0		1.0		ns
t _{ODEH}	Output Data Enable Hold	0.3		0.4		0.4		0.5		0.5		ns
f _{ODESU}	Output Data Enable Setup	1.3		1.5		1.7		2.0		2.0		ns

Notes:

1. The –2 and –3 speed grades have been discontinued. Refer to PDN 0104, PDN 0203, PDN 0604, and PDN 1004 at <http://www.microsemi.com/soc/support/notifications/default.aspx#pdn>.
2. Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing analysis or simulation is required to determine actual worst-case performance. Post-route timing is based on actual routing delay measurements performed on the device prior to shipment.

A1460A, A14V60A Timing Characteristics (continued)

Table 2-33 • A1460A, A14V60A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C

Dedicated (hardwired) I/O Clock Network		–3 Speed ¹		–2 Speed ¹		–1 Speed		Std. Speed		3.3 V Speed ¹		Units
Parameter/Description		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
t _{ILOCKH}	Input Low to High (pad to I/O module input)		2.3		2.6		3.0		3.5		4.5	ns
t _{IOPWH}	Minimum Pulse Width High	2.4		3.2		3.8		4.8		6.5		ns
t _{IPOWL}	Minimum Pulse Width Low	2.4		3.2		3.8		4.8		6.5		ns
t _{IOSAPW}	Minimum Asynchronous Pulse Width	2.4		3.2		3.8		4.8		6.5		ns
t _{ILOCKSW}	Maximum Skew		0.6		0.6		0.6		0.6		0.6	ns
t _{IOP}	Minimum Period	5.0		6.8		8.0		10.0		13.4		ns
f _{IOMAX}	Maximum Frequency		200		150		125		100		75	MHz
Dedicated (hardwired) Array Clock												
t _{HCKH}	Input Low to High (pad to S-module input)		3.7		4.1		4.7		5.5		7.0	ns
t _{HCKL}	Input High to Low (pad to S-module input)		3.7		4.1		4.7		5.5		7.0	ns
t _{HPWH}	Minimum Pulse Width High	2.4		3.2		3.8		4.8		6.5		ns
t _{HPWL}	Minimum Pulse Width Low	2.4		3.2		3.8		4.8		6.5		ns
t _{HCKSW}	Delta High to Low, Low Slew		0.6		0.6		0.6		0.6		0.6	ns
t _{HP}	Minimum Period	5.0		6.8		8.0		10.0		13.4		ns
f _{HMAX}	Maximum Frequency		200		150		125		100		75	MHz
Routed Array Clock Networks												
t _{RCKH}	Input Low to High (FO = 64)		6.0		6.8		7.7		9.0		11.8	ns
t _{RCKL}	Input High to Low (FO = 64)		6.0		6.8		7.7		9.0		11.8	ns
t _{RPWH}	Min. Pulse Width High (FO = 64)	4.1		4.5		5.4		6.1		8.2		ns
t _{RPWL}	Min. Pulse Width Low (FO = 64)	4.1		4.5		5.4		6.1		8.2		ns
t _{RCKSW}	Maximum Skew (FO = 128)		1.2		1.4		1.6		1.8		1.8	ns
t _{RP}	Minimum Period (FO = 64)	8.3		9.3		11.1		12.5		16.7		ns
f _{RMAX}	Maximum Frequency (FO = 64)		120		105		90		80		60	MHz
Clock-to-Clock Skews												
t _{IOHCKSW}	I/O Clock to H-Clock Skew	0.0	2.6	0.0	2.7	0.0	2.9	0.0	3.0	0.0	3.0	ns
t _{IORCKSW}	I/O Clock to R-Clock Skew (FO = 64) (FO = 216)	0.0	1.7	0.0	1.7	0.0	1.7	0.0	1.7	0.0	5.0	ns
		0.0	5.0	0.0	5.0	0.0	5.0	0.0	5.0	0.0	5.0	
t _{HRCKSW}	H-Clock to R-Clock Skew (FO = 64) (FO = 216)	0.0	1.3	0.0	1.0	0.0	1.0	0.0	1.0	0.0	1.0	ns
		0.0	3.0	0.0	3.0	0.0	3.0	0.0	3.0	0.0	3.0	

Notes:

1. The –2 and –3 speed grades have been discontinued. Refer to PDN 0104, PDN 0203, PDN 0604, and PDN 1004 at <http://www.microsemi.com/soc/support/notifications/default.aspx#pdn>.
2. Delays based on 35 pF loading.

A14100A, A14V100A Timing Characteristics (continued)

Table 2-35 • A14100A, A14V100A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C

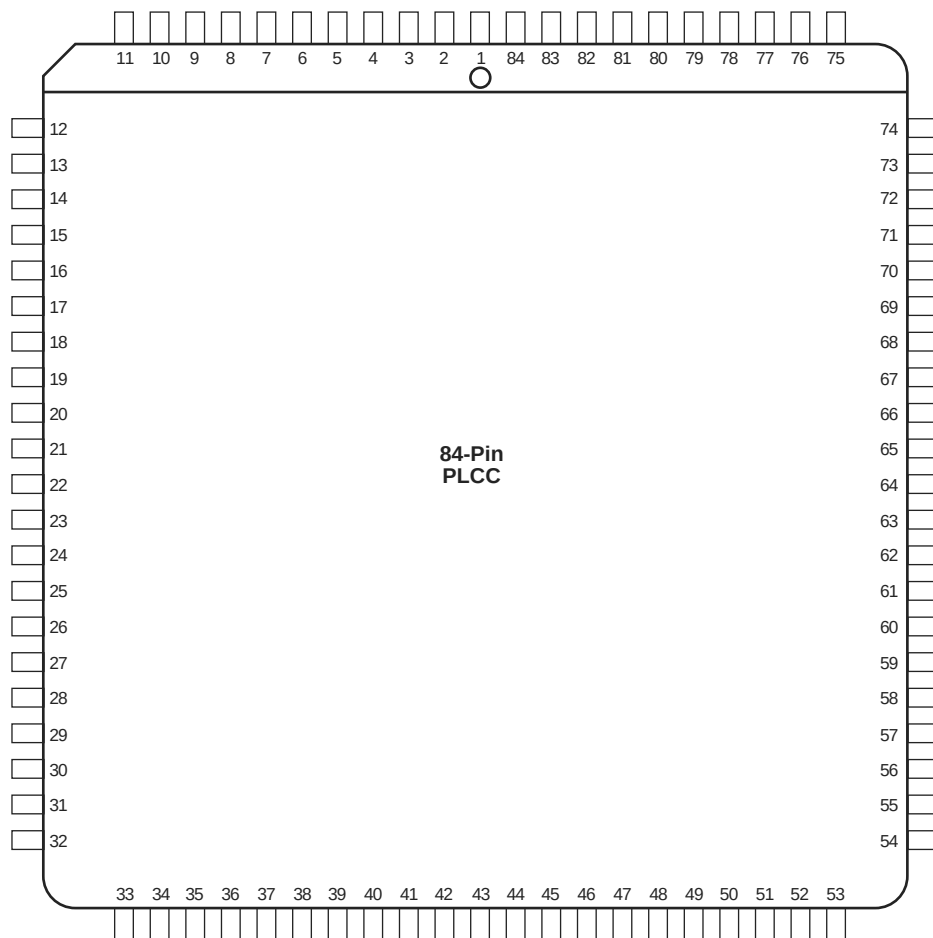
I/O Module Input Propagation Delays		–3 Speed ¹		–2 Speed ¹		–1 Speed		Std. Speed		3.3 V Speed ¹		Units
Parameter/Description		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
t _{INY}	Input Data Pad to Y		2.8		3.2		3.6		4.2		5.5	ns
t _{ICKY}	Input Reg IOCLK Pad to Y		4.7		5.3		6.0		7.0		9.2	ns
t _{OCKY}	Output Reg IOCLK Pad to Y		4.7		5.3		6.0		7.0		9.2	ns
t _{ICLRY}	Input Asynchronous Clear to Y		4.7		5.3		6.0		7.0		9.2	ns
t _{OCLRY}	Output Asynchronous Clear to Y		4.7		5.3		6.0		7.0		9.2	ns
Predicted Input Routing Delays²												
t _{RD1}	FO = 1 Routing Delay		0.9		1.0		1.1		1.3		1.7	ns
t _{RD2}	FO = 2 Routing Delay		1.2		1.4		1.6		1.8		2.4	ns
t _{RD3}	FO = 3 Routing Delay		1.4		1.6		1.8		2.1		2.8	ns
t _{RD4}	FO = 4 Routing Delay		1.7		1.9		2.2		2.5		3.3	ns
t _{RD8}	FO = 8 Routing Delay		2.8		3.2		3.6		4.2		5.5	ns
I/O Module Sequential Timing (wrt IOCLK pad)												
t _{INH}	Input F-F Data Hold	0.0		0.0		0.0		0.0		0.0		ns
t _{INSU}	Input F-F Data Setup	1.2		1.4		1.5		1.8		1.8		ns
t _{IDEH}	Input Data Enable Hold	0.0		0.0		0.0		0.0		0.0		ns
t _{IDESU}	Input Data Enable Setup	5.8		6.5		7.5		8.6		8.6		ns
t _{OUTH}	Output F-F Data hold	0.7		0.8		1.0		1.0		1.0		ns
t _{OUTSU}	Output F-F Data Setup	0.7		0.8		1.0		1.0		1.0		ns
t _{ODEH}	Output Data Enable Hold	0.3		0.4		0.5		0.5		0.5		ns
f _{ODESU}	Output Data Enable Setup	1.3		1.5		2.0		2.0		2.0		ns

Notes: *

1. The –2 and –3 speed grades have been discontinued. Refer to PDN 0104, PDN 0203, PDN 0604, and PDN 1004 at <http://www.microsemi.com/soc/support/notifications/default.aspx#pdn>.
2. Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing analysis or simulation is required to determine actual worst-case performance. Post-route timing is based on actual routing delay measurements performed on the device prior to shipment.

3 – Package Pin Assignments

PL84



Note: This is the top view of the package.

Note

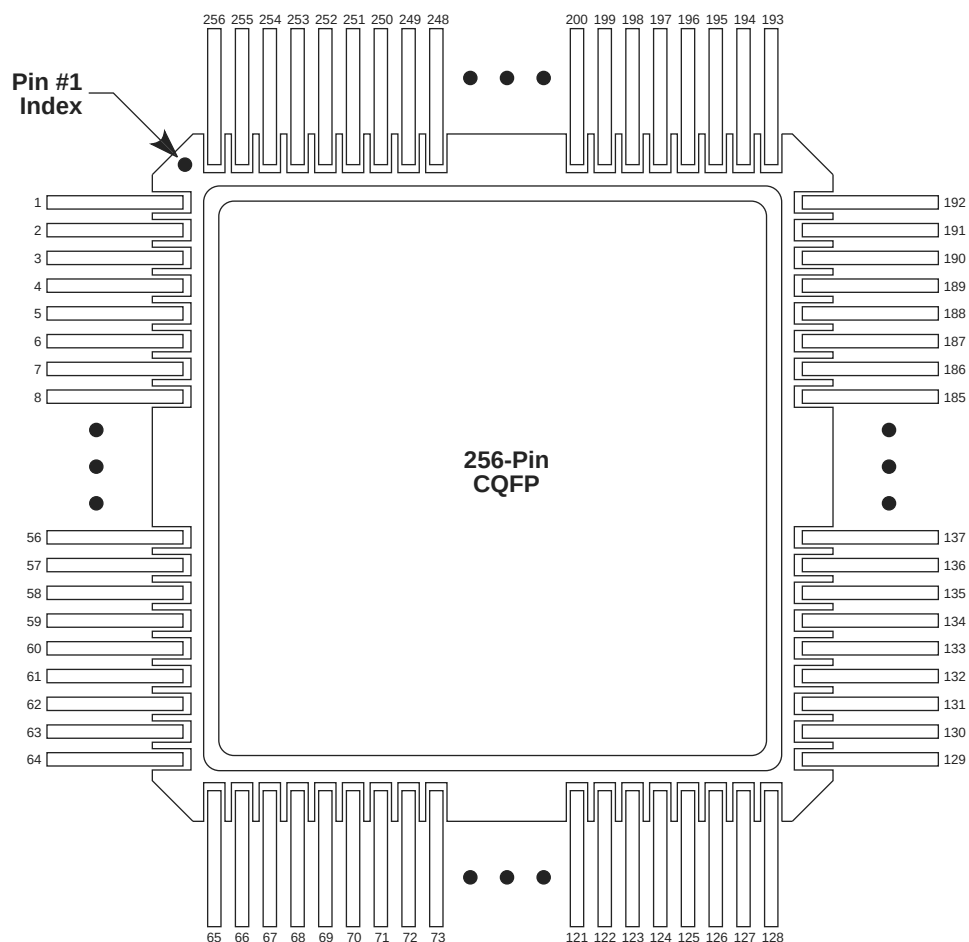
For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/soc/products/solutions/package/docs.aspx>.

PQ160			
Pin Number	A1425, A14V25 Function	A1440, A14V40 Function	A1460, A14V60 Function
92	NC	I/O	I/O
93	NC	I/O	I/O
98	GND	GND	GND
99	VCC	VCC	VCC
100	NC	I/O	I/O
103	GND	GND	GND
107	NC	I/O	I/O
109	NC	I/O	I/O
110	VCC	VCC	VCC
111	GND	GND	GND
112	VCC	VCC	VCC
113	NC	I/O	I/O
119	NC	I/O	I/O
120	IOCLK, I/O	IOCLK, I/O	IOCLK, I/O
121	GND	GND	GND
124	NC	I/O	I/O
127	NC	I/O	I/O
136	CLKA, I/O	CLKA, I/O	CLKA, I/O
137	CLKB, I/O	CLKB, I/O	CLKB, I/O
138	VCC	VCC	VCC
139	GND	GND	GND
140	VCC	VCC	VCC
141	GND	GND	GND
142	PRA, I/O	PRA, I/O	PRA, I/O
143	NC	I/O	I/O
145	NC	I/O	I/O
147	NC	I/O	I/O
149	NC	I/O	I/O
151	NC	I/O	I/O
153	NC	I/O	I/O
154	VCC	VCC	VCC
160	DCLK, I/O	DCLK, I/O	DCLK, I/O

Notes:

1. All unlisted pin numbers are user I/Os.
2. NC denotes no connection.
3. MODE should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

CQ256

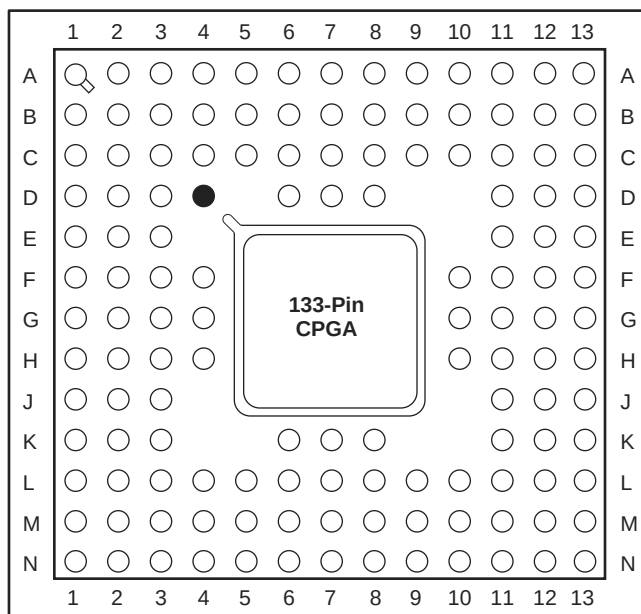


Note: This is the top view.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/soc/products/solutions/package/docs.aspx>

PG133



Note: This is the top view.

Note

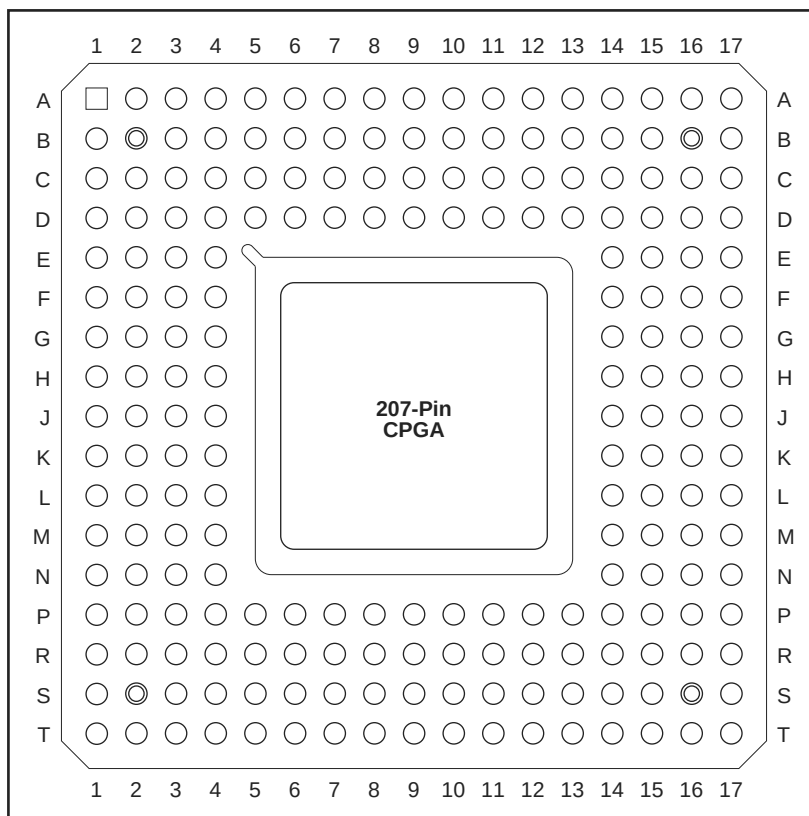
For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/soc/products/solutions/package/docs.aspx>

PG175	
A1440 Function	Location
CLKA or I/O	C9
CLKB or I/O	A9
DCLK or I/O	D5
GND	D4, D8, D11, D12, E4, E14, H4, H12, L4, L12, M4, M8, M12
HCLK or I/O	R8
IOCLK or I/O	E12
IOPCL or I/O	P13
MODE	F3
NC	A1, A2, A15, B2, B3, P2, P14, R1, R2, R14, R15
PRA or I/O	B8
PRB or I/O	R7
SDI or I/O	D3
SDO	N12
VCC	C3, C8, C13, E15, H3, H13, L1, L14, N3, N8, N13

Notes:

1. All unlisted pin numbers are user I/Os.
2. NC denotes no connection.
3. MODE should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.
4. The PG175 package has been discontinued.

PG207



Note: This is the top view.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/soc/products/solutions/package/docs.aspx>



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